

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2988	((Group\$III adj nitride) or (III-v with compound) or (GaN and AlN) or (gallium with aluminum with nitride) or Al\$Ga\$N) and dislocation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/17 16:35
S2	202	S1 and (graded with composition)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/17 14:15
S3	115	S2 and (low with temperature)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/17 14:15
S4	196	((gallium with nitride) or GaN) and ((graded or varying) with (aluminum or Al)) and (sapphire with substrate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/12/17 16:37
S5	315	257/101.ccls.	US-PGPUB; USPAT	OR	ON	2005/12/18 13:12
S6	75	S5 and GaN and AlN	US-PGPUB; USPAT	OR	ON	2005/12/18 13:12
S7	129	S5 and (graded or vary\$3)	US-PGPUB; USPAT	OR	ON	2005/12/18 13:12
S8	37	S6 and (graded or vary\$3)	US-PGPUB; USPAT	OR	ON	2005/12/18 13:28
S9	126	("257"/\$.ccls. or "438"/\$.ccls.) and dislocation and GaN and AlN and ((vary\$3 or graded) with composition)	US-PGPUB; USPAT	OR	ON	2005/12/18 13:29